

Si/SiC Hybrid Modules – EliteSiC, 3 Channel Flying Capacitor Boost 1000 V, 100 A IGBT, 1200 V, 30 A SiC Diode, Q2 Package

NXH300B100H4Q2F2, NXH300B100H4Q2F2SG-R

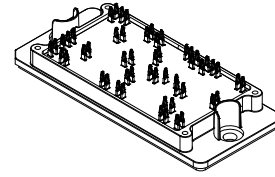
This high-density, integrated power module combines high-performance IGBTs with 1200 V SiC diode.

Features

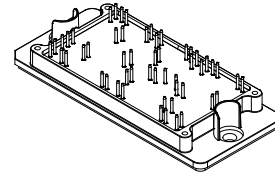
- Extremely Efficient Trench with Field Stop Technology
- Low Switching Loss Reduces System Power Dissipation
- Module Design Offers High Power Density
- Low Inductive Layout
- 3-channel in Q2BOOST Package
- These are Pb-Free Devices

Typical Applications

- Solar Inverter
- Uninterruptible Power Supplies

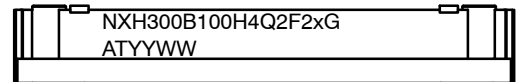


PIM53, 93x47 (PRESSFIT)
CASE 180CB



PIM53, 93x47 (SOLDER PIN)
CASE 180CC

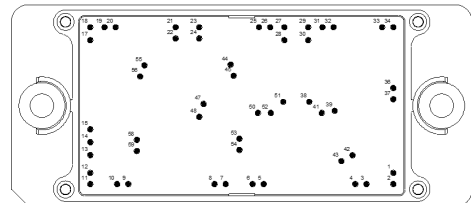
MARKING DIAGRAM



NXH300B100H4Q2F2x = Specific Device Code
(x = P, S)

AT = Assembly & Test Site Code
YYWW = Year and Work Week Code

PIN CONNECTION



ORDERING INFORMATION

See detailed ordering and shipping information on page 11 of this data sheet.

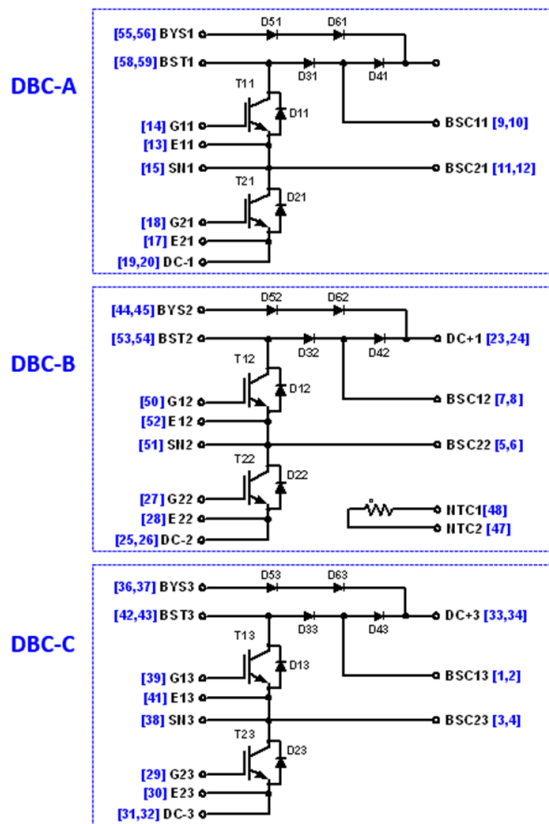


Figure 1. NXH300B100H4Q2F2PG/SG/SG-R Schematic Diagram

NXH300B100H4Q2F2, NXH300B100H4Q2F2SG-R

ABSOLUTE MAXIMUM RATINGS (Note 1) ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Symbol | Parameter | Value | Unit |
|--|--|----------------|------------------|
| IGBT (T11, T21, T12, T22, T13, T23) | | | |
| V_{CES} | Collector-Emitter voltage | 1000 | V |
| V_{GE} | Gate-Emitter Voltage Positive transient gate-emitter voltage ($T_{pulse} = 5 \mu\text{s}$, $D < 0.10$) | ± 20 30 | V |
| I_C | Continuous Collector Current (@ $V_{GE} = 20 \text{ V}$, $T_C = 80^\circ\text{C}$) | 73 | A |
| $I_{C(Pulse)}$ | Pulsed Peak Collector Current @ $T_C = 80^\circ\text{C}$ ($T_J = 150^\circ\text{C}$) | 219 | A |
| P_{tot} | Power Dissipation ($T_J = 150^\circ\text{C}$, $T_C = 80^\circ\text{C}$) | 194 | W |
| T_{JMIN} | Minimum Operating Junction Temperature | -40 | $^\circ\text{C}$ |
| T_{JMAX} | Maximum Operating Junction Temperature | 175 | $^\circ\text{C}$ |

IGBT INVERSE DIODE (D11, D21, D12, D22, D13, D23) AND BYPASS DIODE (D51, D61, D52, D62, D53, D63)

| | | | |
|------------|---|------|------------------|
| V_{RRM} | Peak Repetitive Reverse Voltage | 1600 | V |
| I_F | Continuous Forward Current @ $T_C = 80^\circ\text{C}$ | 36 | A |
| I_{FRM} | Repetitive Peak Forward Current ($T_J = 150^\circ\text{C}$, T_J limited by T_{Jmax}) | 108 | A |
| P_{tot} | Maximum Power Dissipation @ $T_C = 80^\circ\text{C}$ ($T_J = 150^\circ\text{C}$) | 79 | W |
| T_{JMIN} | Minimum Operating Junction Temperature | -40 | $^\circ\text{C}$ |
| T_{JMAX} | Maximum Operating Junction Temperature | 150 | $^\circ\text{C}$ |

BOOST SILICON CARBIDE SCHOTTKY DIODE (D31, D41, D32, D42, D33, D43)

| | | | |
|------------|---|------|------------------|
| V_{RRM} | Peak Repetitive Reverse Voltage | 1200 | V |
| I_F | Continuous Forward Current @ $T_C = 80^\circ\text{C}$ | 36 | A |
| I_{FRM} | Repetitive Peak Forward Current ($T_J = 150^\circ\text{C}$, T_J limited by T_{Jmax}) | 108 | A |
| P_{tot} | Maximum Power Dissipation @ $T_C = 80^\circ\text{C}$ ($T_J = 150^\circ\text{C}$) | 104 | W |
| T_{JMIN} | Minimum Operating Junction Temperature | -40 | $^\circ\text{C}$ |
| T_{JMAX} | Maximum Operating Junction Temperature | 175 | $^\circ\text{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for Safe Operating parameters.

THERMAL AND INSULATION PROPERTIES (Note 1) ($T_J = 25^\circ\text{C}$ unless otherwise noted)

| Symbol | Rating | Value | Unit |
|---------------------------|---|------------|------------------|
| THERMAL PROPERTIES | | | |
| T_{VJOP} | Operating Temperature under Switching Condition | -40 to 150 | $^\circ\text{C}$ |
| T_{stg} | Storage Temperature Range | -40 to 125 | $^\circ\text{C}$ |

INSULATION PROPERTIES

| | | | |
|----------|--|------|-----------|
| V_{is} | Isolation Test Voltage, $t = 2 \text{ sec}$, 50 Hz (Note 3) | 4000 | V_{RMS} |
| | Creepage Distance | 12.7 | mm |
| CTI | Comparative Tracking Index | >600 | |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for Safe Operating parameters.
3. 4000 V_{ACRMS} for 1 second duration is equivalent to 3333 V_{ACRMS} for 1 minute duration.

NXH300B100H4Q2F2, NXH300B100H4Q2F2SG-R

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

| Symbol | Parameter | Test Condition | Min | Typ | Max | Unit |
|--|---------------------------------------|---|------|-------|------|------|
| IGBT (T11, T21, T12, T22, T13, T23) | | | | | | |
| V _{(BR)CES} | Collector-Emitter Breakdown Voltage | V _{GE} = 0 V, I _C = 1 mA | 1000 | 1118 | – | V |
| V _{CE(SAT)} | Collector-Emitter Saturation Voltage | V _{GE} = 15 V, I _C = 100 A, T _C = 25°C | – | 1.80 | 2.25 | V |
| | | V _{GE} = 15 V, I _C = 100 A, T _C = 150°C | – | 2.03 | – | |
| V _{GE(TH)} | Gate-Emitter Threshold Voltage | V _{GE} = V _{CE} , I _C = 100 mA | 4.1 | 5.08 | 5.9 | V |
| I _{CES} | Collector-Emitter Cutoff Current | V _{GE} = 0 V, V _{CE} = 1000 V | – | – | 800 | μA |
| I _{GES} | Gate Leakage Current | V _{GE} = ±20 V, V _{CE} = 0 V | – | – | ±400 | nA |
| r _g | Internal Gate Resistor | | – | 5 | – | Ω |
| t _{d(on)} | Turn-On Delay Time | T _J = 25°C V _{CE} = 600 V, I _C = 50 A V _{GE} = -9 V, +15 V, R _G = 6 Ω | – | 95 | – | ns |
| t _r | Rise Time | | – | 15.42 | – | |
| t _{d(off)} | Turn-Off Delay Time | | – | 267 | – | |
| t _f | Fall time | | – | 59 | – | |
| E _{on} | Turn on switching loss | | – | 1030 | – | |
| E _{off} | Turn off switching loss | – | 1200 | – | μJ | |
| t _{d(on)} | Turn-On Delay Time | T _J = 125°C V _{CE} = 600 V, I _C = 50 A V _{GE} = -9 V, +15 V, R _G = 6 Ω | – | 97 | – | ns |
| t _r | Rise Time | | – | 18 | – | |
| t _{d(off)} | Turn-Off Delay Time | | – | 314 | – | |
| t _f | Fall time | | – | 93 | – | |
| E _{on} | Turn on switching loss | | – | 1260 | – | |
| E _{off} | Turn off switching loss | – | 2140 | – | μJ | |
| C _{ies} | Input capacitance | V _{CE} = 20 V, V _{GE} = 0 V, f = 1 MHz | – | 6323 | – | pF |
| C _{oes} | Output capacitance | | – | 241 | – | |
| C _{res} | Reverse transfer capacitance | | – | 34 | – | |
| Q _g | Gate Charge | V _{CE} = 600 V, V _{GE} = -15/+15 V, I _C = 75 A | – | 340 | – | nC |
| R _{thJH} | Thermal Resistance – chip-to-heatsink | Thermal grease, Thickness = 2.1 Mil ±2% λ = 2.9 W/mK | – | 0.66 | – | K/W |
| R _{thJC} | Thermal Resistance – chip-to-case | | – | 0.48 | – | K/W |

IGBT INVERSE DIODE (D11, D21, D12, D22, D13, D23) AND BYPASS DIODE (D51, D61, D52, D62, D53, D63)

| | | | | | | |
|-------------------|---------------------------------------|---|---|------|-----|-----|
| V _F | Diode Forward Voltage | I _F = 30 A, T _J = 25°C | – | 1.04 | 1.7 | V |
| | | I _F = 30 A, T _J = 150°C | – | 0.94 | – | |
| R _{thJH} | Thermal Resistance – chip-to-heatsink | Thermal grease, Thickness = 2.1 Mil ±2% λ = 2.9 W/mK | – | 1.04 | – | K/W |

BOOST SILICON CARBIDE SCHOTTKY DIODE (D31, D41, D32, D42, D33, D43)

| | | | | | | |
|------------------|---------------------------------------|---|---|------|-----|------|
| I _R | Diode Reverse Leakage Current | V _R = 1200 V, T _J = 25°C | – | – | 600 | μA |
| V _F | Diode Forward Voltage | I _F = 30 A, T _J = 25°C | – | 1.42 | 1.7 | V |
| | | I _F = 30 A, T _J = 150°C | – | 1.85 | – | |
| t _{rr} | Reverse Recovery Time | T _J = 25°C V _{DS} = 600 V, I _C = 50 A V _{GE} = -9 V, 15 V, R _G = 1 Ω | – | 15 | – | ns |
| Q _{rr} | Reverse Recovery Charge | | – | 128 | – | nC |
| I _{RRM} | Peak Reverse Recovery Current | | – | 13 | – | A |
| di/dt | Peak Rate of Fall of Recovery Current | | – | 4200 | – | A/μs |
| E _{rr} | Reverse Recovery Energy | | – | 16 | – | μJ |

NXH300B100H4Q2F2, NXH300B100H4Q2F2SG-R

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted) (continued)

| Symbol | Parameter | Test Condition | Min | Typ | Max | Unit |
|--|---------------------------------------|--|-----|------|-----|------------------|
| BOOST SILICON CARBIDE SCHOTTKY DIODE (D31, D41, D32, D42, D33, D43) | | | | | | |
| t_{rr} | Reverse Recovery Time | $T_J = 125^\circ\text{C}$ $V_{DS} = 600\text{ V}$, $I_C = 50\text{ A}$ $V_{GE} = -9\text{ V}$, 15 V , $R_G = 1\ \Omega$ | - | 19 | - | ns |
| Q_{rr} | Reverse Recovery Charge | | - | 175 | - | nC |
| I_{RRM} | Peak Reverse Recovery Current | | - | 17 | - | A |
| di/dt | Peak Rate of Fall of Recovery Current | | - | 3153 | - | A/ μs |
| E_{rr} | Reverse Recovery Energy | | - | 18 | - | μJ |
| R_{thJH} | Thermal Resistance - chip-to-heatsink | Thermal grease, Thickness = 2.1 Mil $\pm 2\%$ $\lambda = 2.9\text{ W/mK}$ | - | 0.85 | - | K/W |
| R_{thJC} | Thermal Resistance - chip-to-case | | - | 0.73 | - | K/W |

THERMISTOR CHARACTERISTICS

| | | | | | | |
|--------------|----------------------------|---------------------------------|----|------|---|------------|
| R_{25} | Nominal resistance | | - | 22 | - | k Ω |
| R_{100} | Nominal resistance | $T = 100^\circ\text{C}$ | - | 1486 | - | Ω |
| $\Delta R/R$ | Deviation of R_{25} | | -5 | - | 5 | % |
| P_D | Power dissipation | | - | 200 | - | mW |
| | Power dissipation constant | | - | 2 | - | mW/K |
| | B-value | B (25/50), tolerance $\pm 3\%$ | - | 3950 | - | K |
| | B-value | B (25/100), tolerance $\pm 3\%$ | - | 3998 | - | K |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NXH300B100H4Q2F2, NXH300B100H4Q2F2SG-R

TYPICAL CHARACTERISTICS – IGBT, INVERSE & BYPASS DIODE AND BOOST DIODE

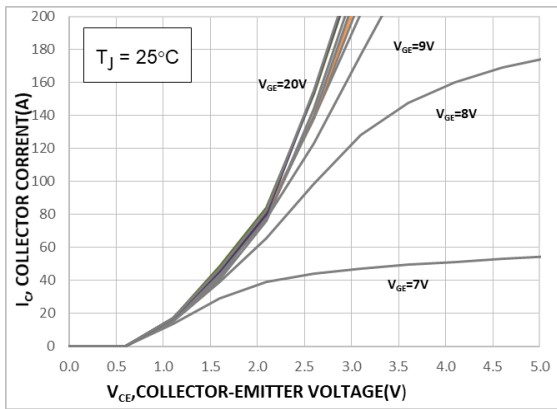


Figure 2. Typical Output Characteristics

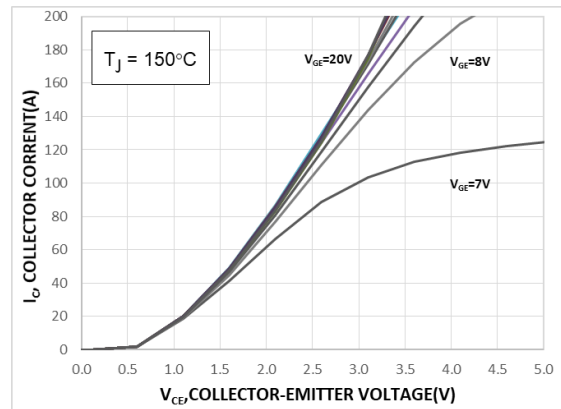


Figure 3. Typical Output Characteristics

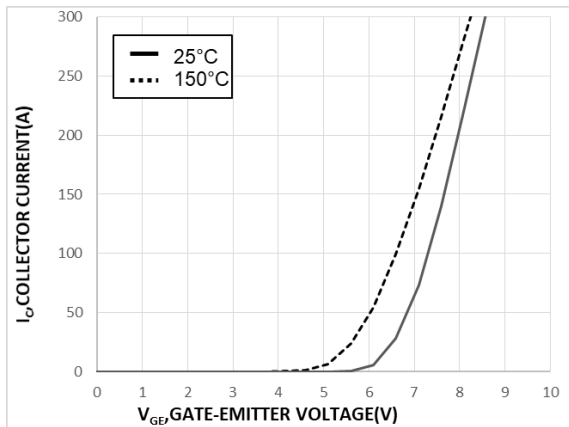


Figure 4. Transfer Characteristics

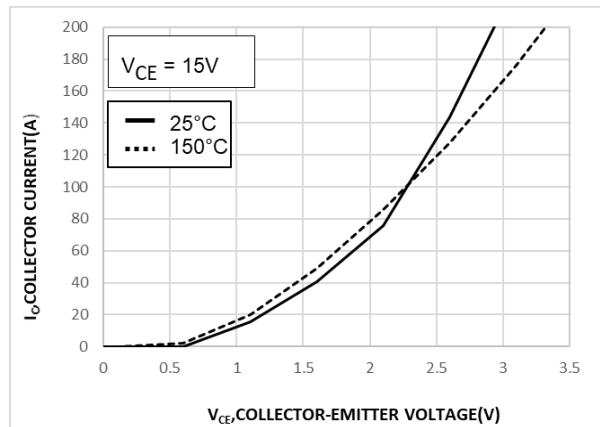


Figure 5. Typical Saturation Voltage Characteristics

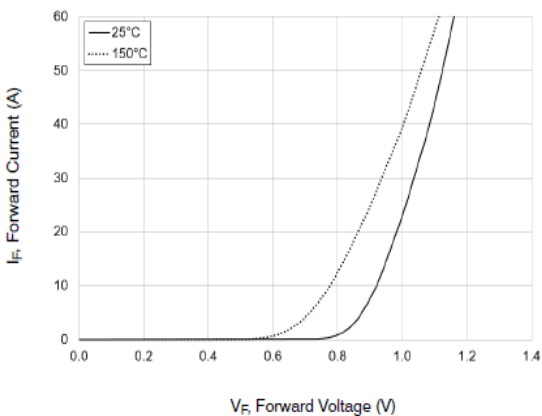


Figure 6. Inverse Diode Forward Characteristics

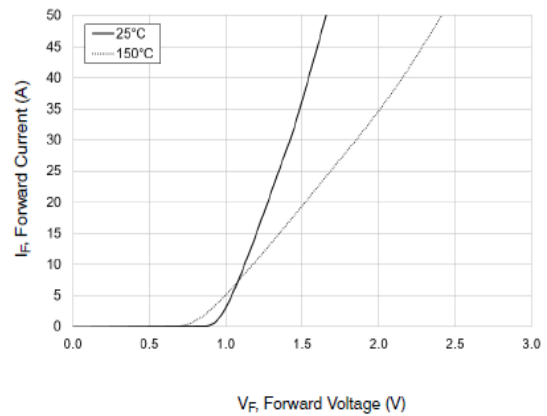


Figure 7. Boost Diode Forward Characteristics

TYPICAL CHARACTERISTICS – IGBT, INVERSE & BYPASS DIODE AND BOOST DIODE (CONTINUED)

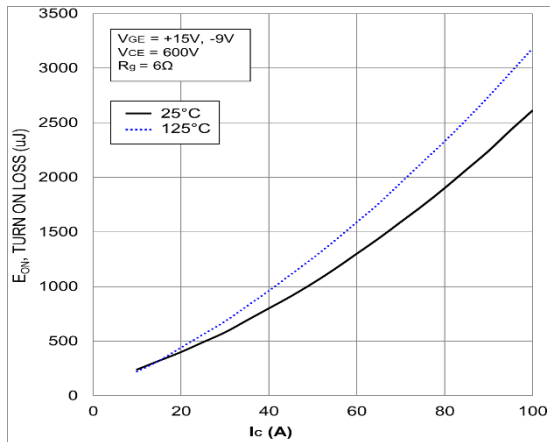


Figure 8. Typical Turn On Loss vs. I_c

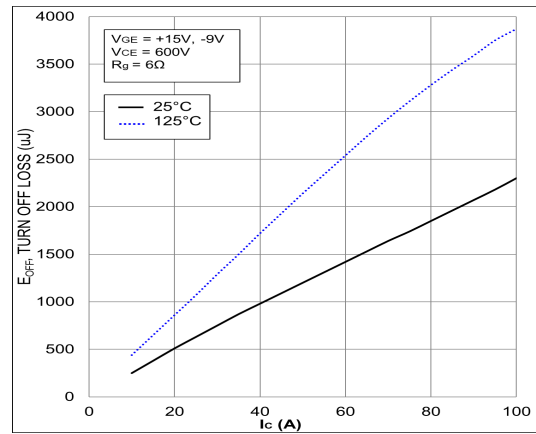


Figure 9. Typical Turn Off Loss vs. I_c

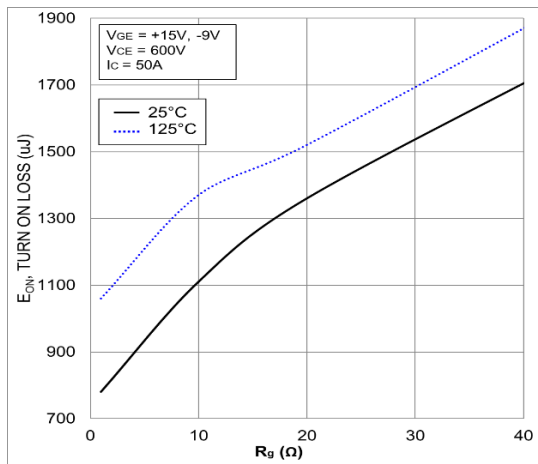


Figure 10. Typical Turn On Loss vs. R_g

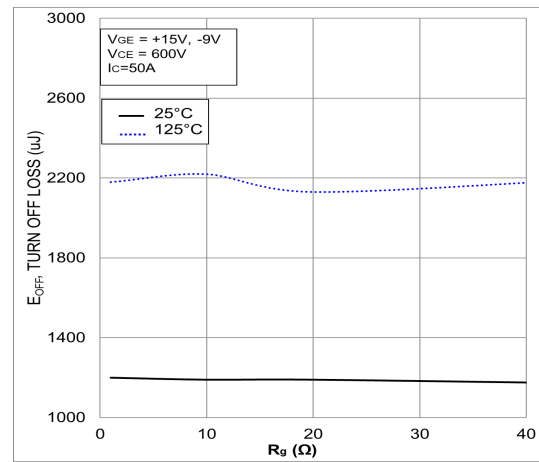


Figure 11. Typical Turn Off Loss vs. R_g

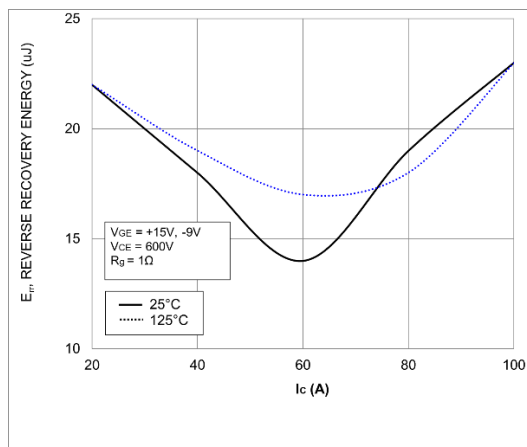


Figure 12. Typical Reverse Recovery Energy Loss vs. I_c

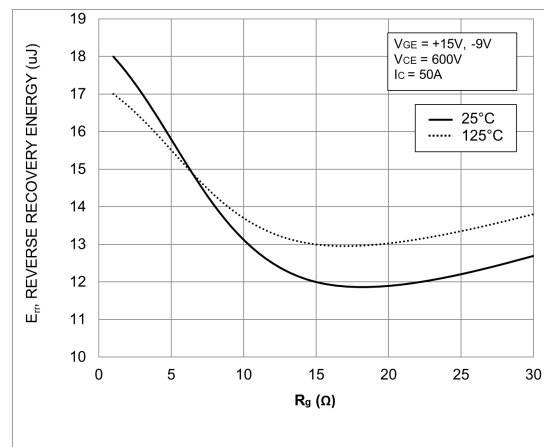


Figure 13. Typical Reverse Recovery Energy Loss vs. R_g

NXH300B100H4Q2F2, NXH300B100H4Q2F2SG-R

TYPICAL CHARACTERISTICS – IGBT, INVERSE & BYPASS DIODE AND BOOST DIODE (CONTINUED)

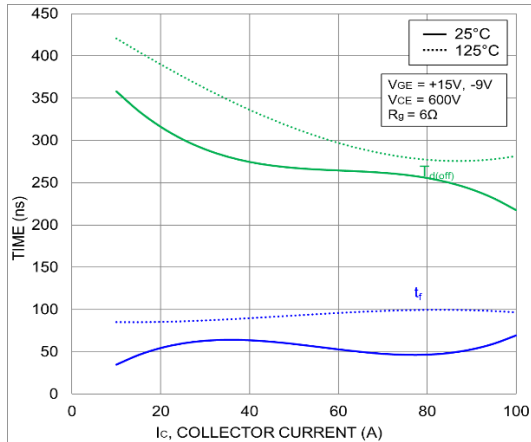


Figure 14. Typical Turn-Off Switching Time vs. I_c

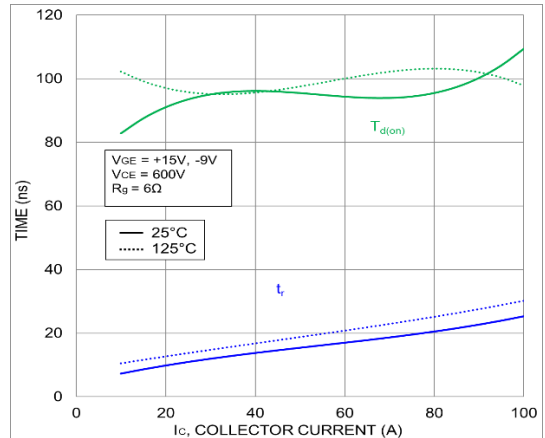


Figure 15. Typical Turn-On Switching Time vs. I_c

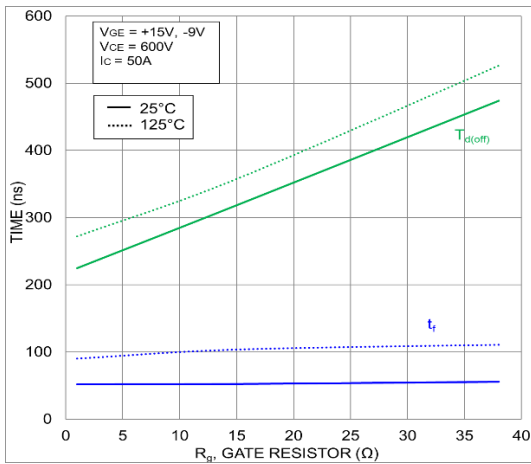


Figure 16. Typical Turn-Off Switching Time vs. R_g

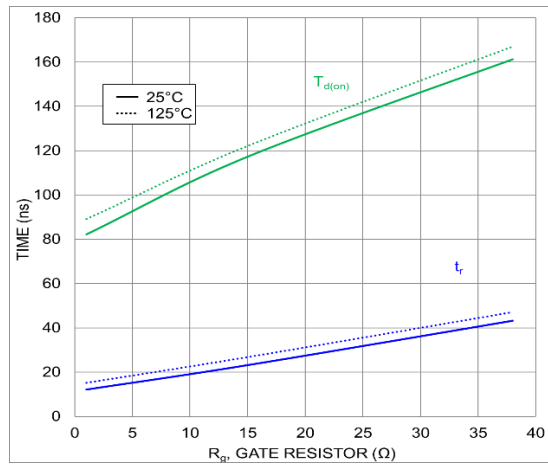


Figure 17. Typical Turn-On Switching Time vs. R_g

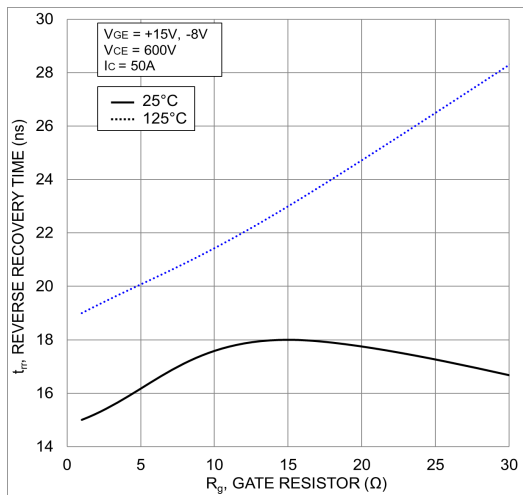


Figure 18. Typical Reverse Recovery Time vs. R_g

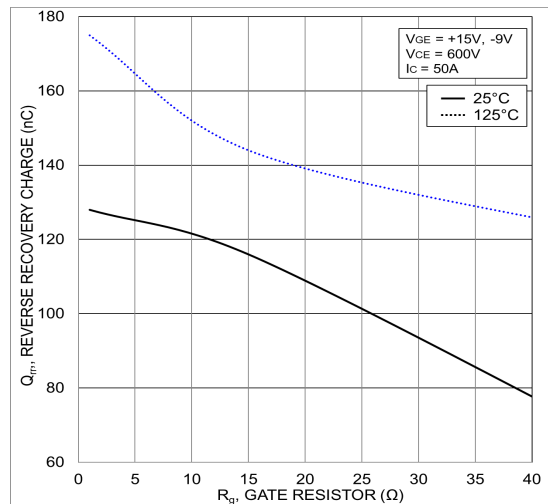


Figure 19. Typical Reverse Recovery Charge vs. R_g

NXH300B100H4Q2F2, NXH300B100H4Q2F2SG-R

TYPICAL CHARACTERISTICS – IGBT, INVERSE & BYPASS DIODE AND BOOST DIODE (CONTINUED)

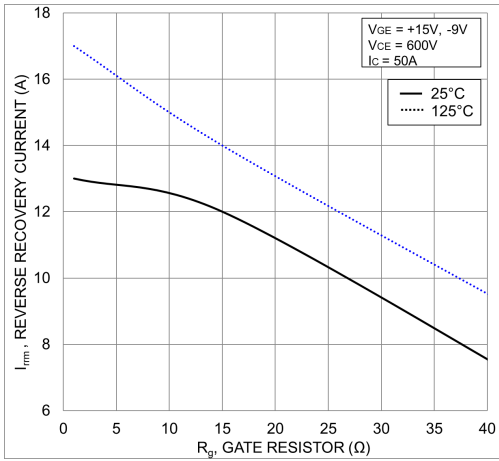


Figure 20. Typical Reverse Recovery Peak Current vs. R_g

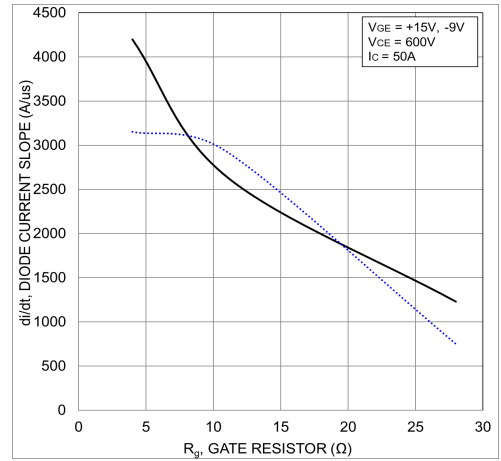


Figure 21. Typical di/dt vs. R_g

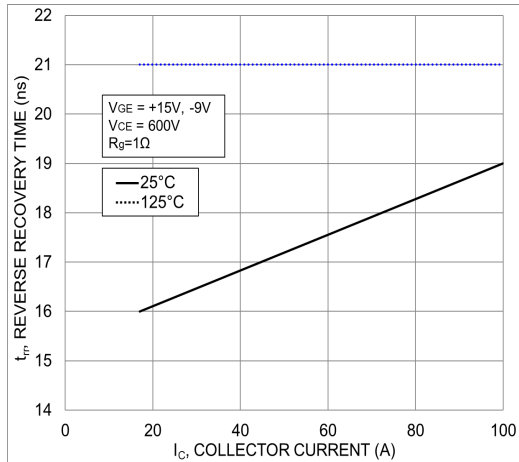


Figure 22. Typical Reverse Recovery Time vs. I_C

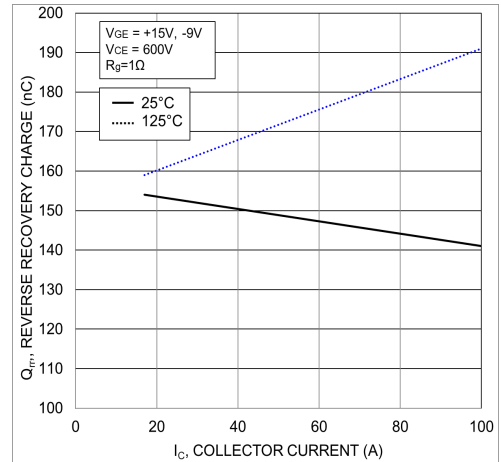


Figure 23. Typical Reverse Recovery Charge vs. I_C

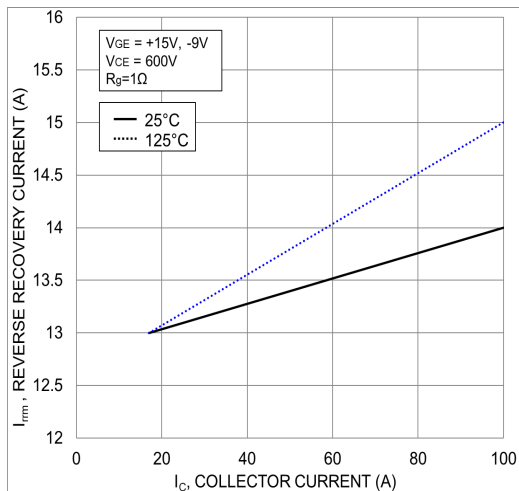


Figure 24. Typical Reverse Recovery Current vs. I_C

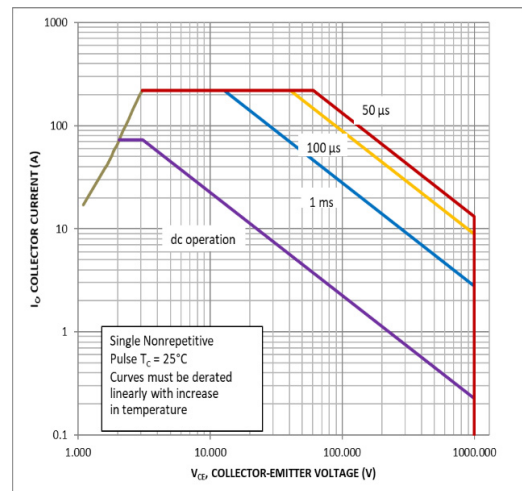


Figure 25. FBSOA

NXH300B100H4Q2F2, NXH300B100H4Q2F2SG-R

TYPICAL CHARACTERISTICS – IGBT, INVERSE & BYPASS DIODE AND BOOST DIODE (CONTINUED)

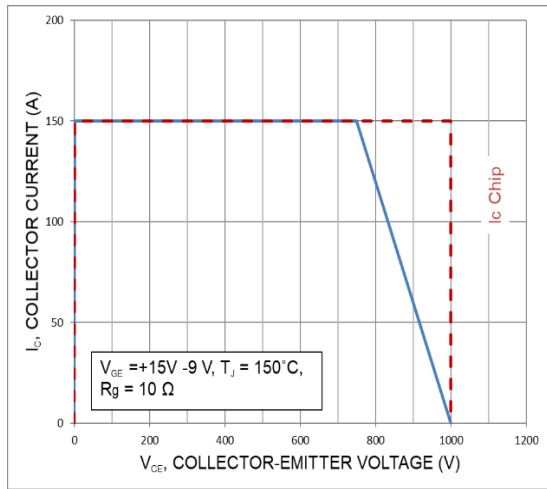


Figure 26. RBSOA

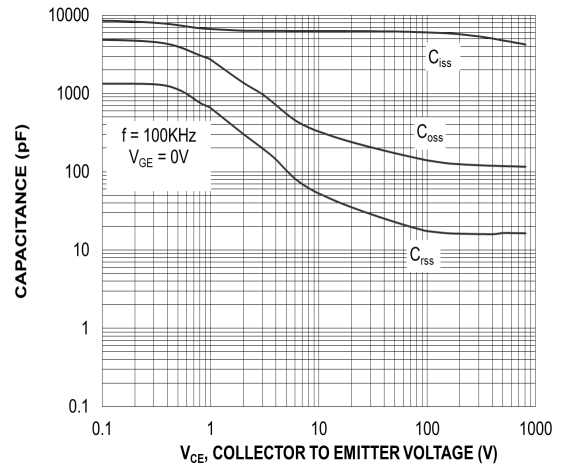


Figure 27. Capacitance Charge

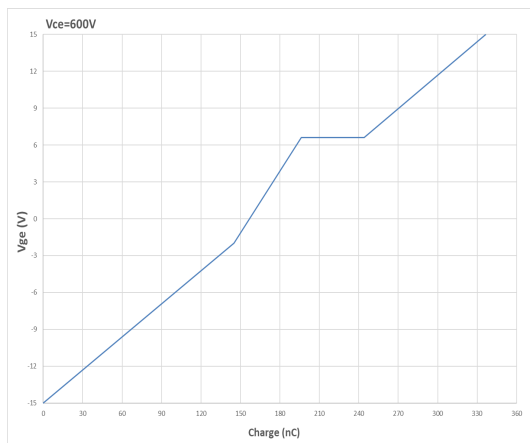


Figure 28. Gate Voltage vs. Gate Charge

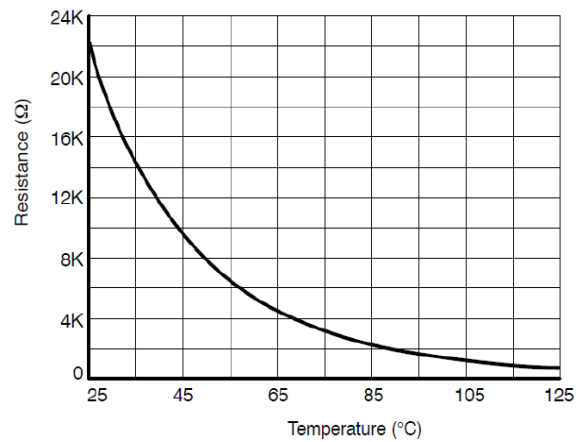


Figure 29. NTC Characteristics

NXH300B100H4Q2F2, NXH300B100H4Q2F2SG-R

TYPICAL CHARACTERISTICS – IGBT, INVERSE & BYPASS DIODE AND BOOST DIODE (CONTINUED)

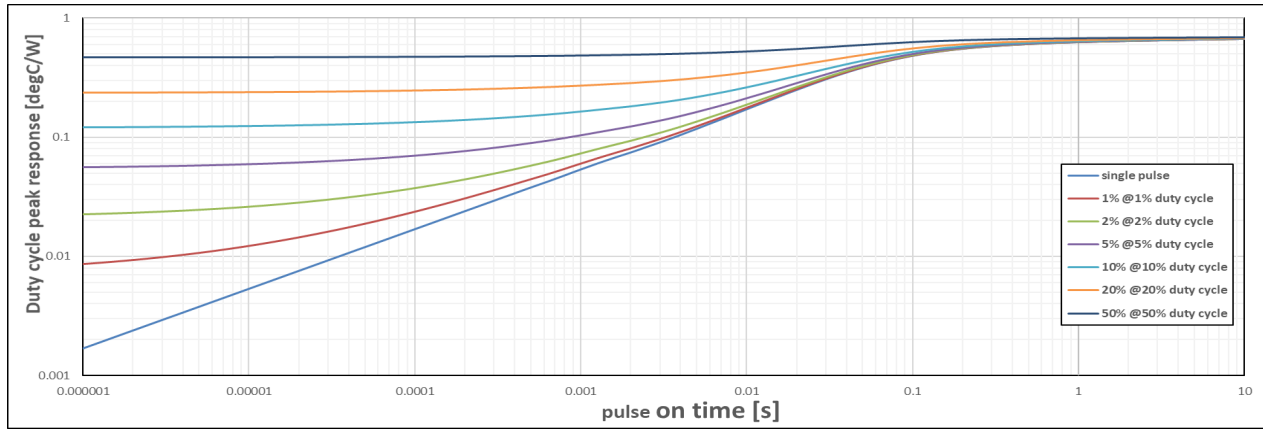


Figure 30. Transient Thermal Impedance (IGBT)

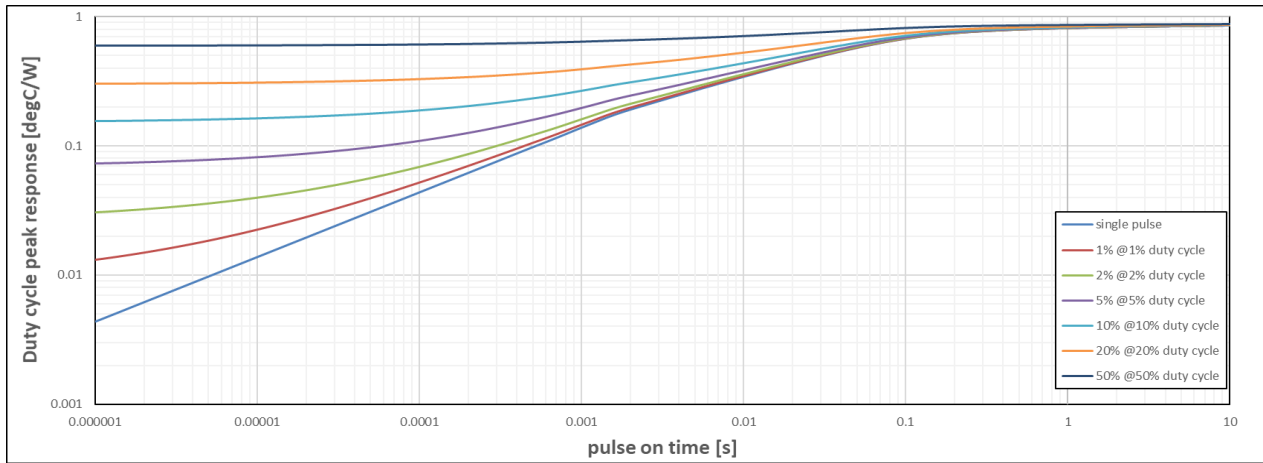


Figure 31. Transient Thermal Impedance (BOOST DIODE)

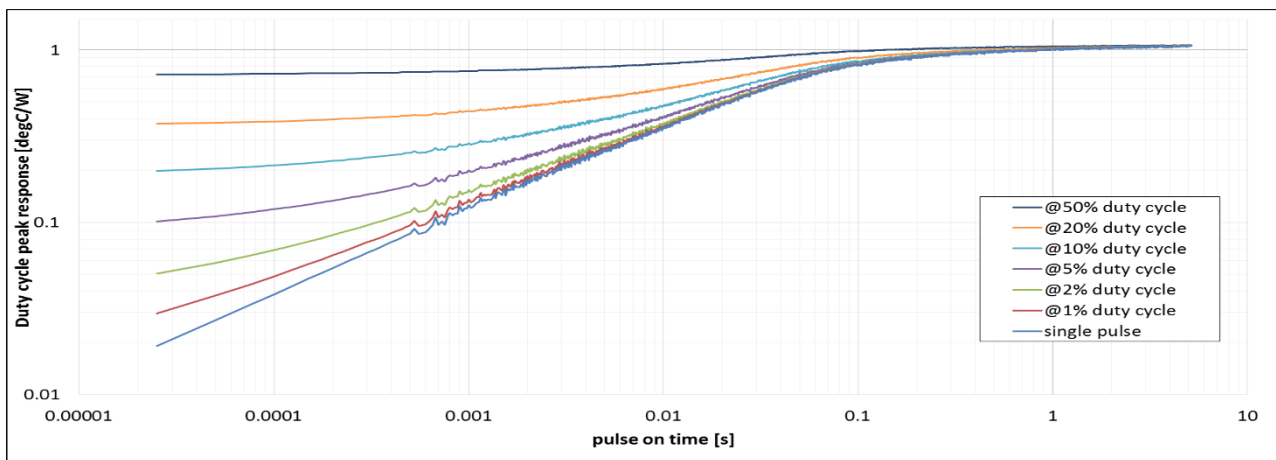


Figure 32. Transient Thermal Impedance (INVERSE&BYPASS DIODE)

NXH300B100H4Q2F2, NXH300B100H4Q2F2SG-R

ORDERING INFORMATION

| Orderable Part Number | Marking | Package | Shipping |
|--|---|---|-------------------------|
| NXH300B100H4Q2F2PG PRESS FIT PINS | NXH300B100H4Q2F2PG | Q2BOOST - PIM53, 93x47 (PRESSFIT) (Pb-Free and Halide-Free Press Fit Pins) | 12 Units / Blister Tray |
| NXH300B100H4Q2F2SG, NXH300B100H4Q2F2SG-R SOLDER PINS | NXH300B100H4Q2F2SG, NXH300B100H4Q2F2SG-R | Q2BOOST - PIM53, 93x47 (SOLDER PIN) (Pb-Free and Halide-Free Solder Pins) | 12 Units / Blister Tray |

MECHANICAL CASE OUTLINE

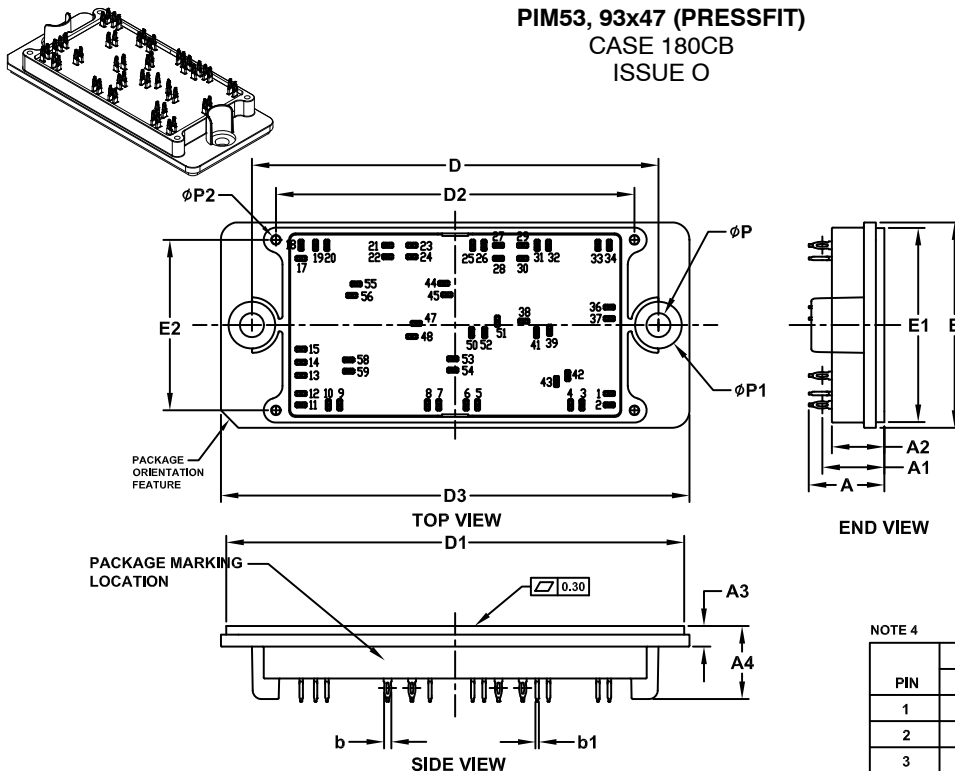
PACKAGE DIMENSIONS

ON Semiconductor®

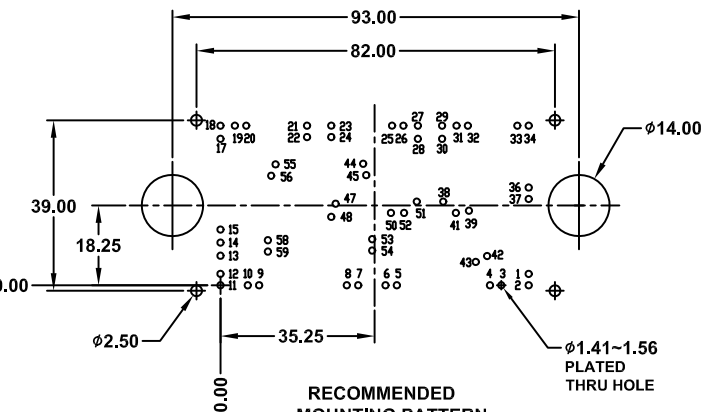


PIM53, 93x47 (PRESSFIT) CASE 180CB ISSUE O

DATE 30 APR 2020



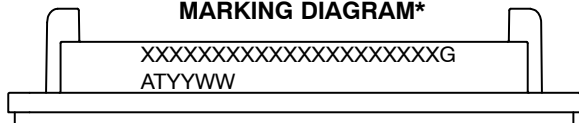
| DIM | MILLIMETERS | | |
|-----|-------------|--------|--------|
| | MIN. | NOM. | MAX. |
| A | 16.90 | 17.30 | 17.70 |
| A1 | 13.97 | 14.18 | 14.39 |
| A2 | 11.70 | 12.00 | 12.30 |
| A3 | 4.40 | 4.70 | 5.00 |
| A4 | 16.40 | 16.70 | 17.00 |
| b | 1.61 | 1.66 | 1.71 |
| b1 | 0.75 | 0.80 | 0.85 |
| D | 92.90 | 93.00 | 93.10 |
| D1 | 104.45 | 104.75 | 105.05 |
| D2 | 81.80 | 82.00 | 82.20 |
| D3 | 106.90 | 107.20 | 107.50 |
| E | 46.70 | 47.00 | 47.30 |
| E1 | 44.10 | 44.40 | 44.70 |
| E2 | 38.80 | 39.00 | 39.20 |
| P | 5.40 | 5.50 | 5.60 |
| P1 | 10.60 | 10.70 | 10.80 |
| P2 | 1.80 | 2.00 | 2.20 |



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009
2. CONTROLLING DIMENSION : MILLIMETERS
3. DIMENSIONS b AND b1 APPLY TO THE PLATED TERMINALS AND ARE MEASURED AT DIMENSION A1
4. PIN POSITION TOLERANCE IS $\pm 0.4\text{mm}$
5. PACKAGE MARKING IS LOCATED AS SHOWN ON THE SIDE OPPOSITE THE PACKAGE ORIENTATION FEATURES

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
 G = Pb-Free Package
 AT = Assembly & Test Site Code
 YYWW = Year and Work Week Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

NOTE 4

| PIN | PIN POSITION | | PIN | PIN POSITION | |
|-----|--------------|-------|-----|--------------|-------|
| | X | Y | | X | Y |
| 1 | 70.50 | 2.60 | 29 | 50.70 | 36.50 |
| 2 | 70.50 | 0.00 | 30 | 50.70 | 33.50 |
| 3 | 64.25 | 0.00 | 31 | 54.00 | 36.50 |
| 4 | 61.65 | 0.00 | 32 | 56.60 | 36.50 |
| 5 | 40.35 | 0.00 | 33 | 67.90 | 36.50 |
| 6 | 37.75 | 0.00 | 34 | 70.50 | 36.50 |
| 7 | 31.50 | 0.00 | 36 | 70.50 | 22.35 |
| 8 | 28.90 | 0.00 | 37 | 70.50 | 19.75 |
| 9 | 8.85 | 0.00 | 38 | 50.95 | 19.15 |
| 10 | 6.25 | 0.00 | 39 | 56.85 | 17.05 |
| 11 | 0.00 | 0.00 | 41 | 53.85 | 16.55 |
| 12 | 0.00 | 2.60 | 42 | 61.00 | 6.70 |
| 13 | 0.00 | 6.75 | 43 | 58.40 | 5.35 |
| 14 | 0.00 | 9.75 | 44 | 32.65 | 27.80 |
| 15 | 0.00 | 12.75 | 45 | 33.35 | 25.20 |
| 17 | 0.00 | 33.50 | 47 | 26.35 | 18.65 |
| 18 | 0.00 | 36.50 | 48 | 25.35 | 15.65 |
| 19 | 3.30 | 36.50 | 50 | 39.00 | 16.55 |
| 20 | 5.90 | 36.50 | 51 | 44.90 | 19.15 |
| 21 | 19.80 | 36.50 | 52 | 42.00 | 16.55 |
| 22 | 19.80 | 33.90 | 53 | 34.70 | 10.55 |
| 23 | 25.35 | 36.50 | 54 | 34.70 | 7.95 |
| 24 | 25.35 | 33.90 | 55 | 12.60 | 27.65 |
| 25 | 39.25 | 36.50 | 56 | 11.60 | 25.05 |
| 26 | 41.85 | 36.50 | 58 | 10.85 | 10.30 |
| 27 | 45.15 | 36.50 | 59 | 10.85 | 7.70 |
| 28 | 45.15 | 33.50 | | | |

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| DESCRIPTION: | PIM53 93X47 (PRESS FIT) | PAGE 1 OF 1 |

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MECHANICAL CASE OUTLINE

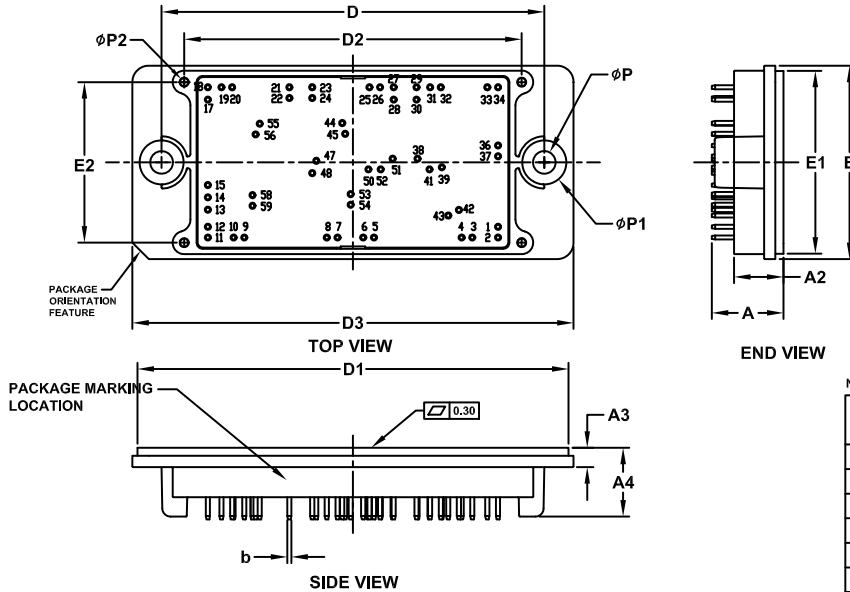
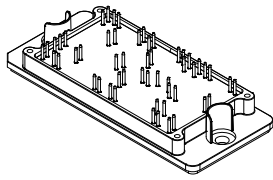
PACKAGE DIMENSIONS

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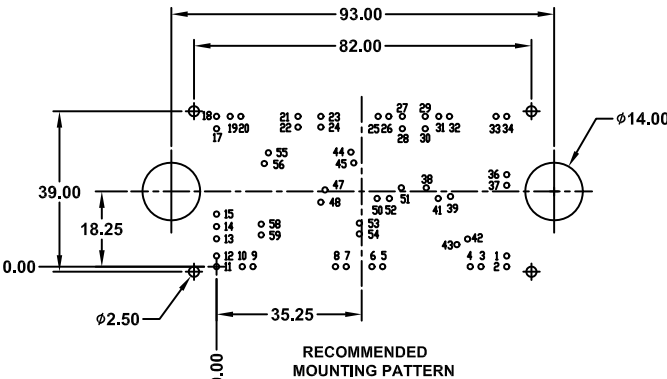


PIM53, 93x47 (SOLDER PIN) CASE 180CC ISSUE O

DATE 04 MAY 2020



| DIM | MILLIMETERS | | |
|-----|-------------|--------|--------|
| | MIN. | NOM. | MAX. |
| A | 16.80 | 17.20 | 17.60 |
| A2 | 11.70 | 12.00 | 12.30 |
| A3 | 4.40 | 4.70 | 5.00 |
| A4 | 16.40 | 16.70 | 17.00 |
| b | 0.95 | 1.00 | 1.05 |
| D | 92.90 | 93.00 | 93.10 |
| D1 | 104.45 | 104.75 | 105.05 |
| D2 | 81.80 | 82.00 | 82.20 |
| D3 | 106.90 | 107.20 | 107.50 |
| E | 46.70 | 47.00 | 47.30 |
| E1 | 44.10 | 44.40 | 44.70 |
| E2 | 38.80 | 39.00 | 39.20 |
| P | 5.40 | 5.50 | 5.60 |
| P1 | 10.60 | 10.70 | 10.80 |
| P2 | 1.80 | 2.00 | 2.20 |

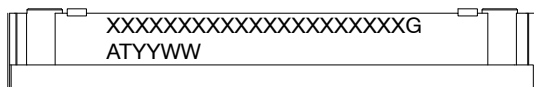


RECOMMENDED MOUNTING PATTERN
* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009
2. CONTROLLING DIMENSION : MILLIMETERS
3. DIMENSIONS b AND b1 APPLY TO THE PLATED TERMINALS AND ARE MEASURED AT DIMENSION A1
4. PIN POSITION TOLERANCE IS ± 0.4mm
5. PACKAGE MARKING IS LOCATED AS SHOWN ON THE SIDE OPPOSITE THE PACKAGE ORIENTATION FEATURES

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
G = Pb-Free Package
AT = Assembly & Test Site Code
YYWW= Year and Work Week Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

NOTE 4

| PIN | PIN POSITION | | PIN | PIN POSITION | |
|-----|--------------|-------|-----|--------------|-------|
| | X | Y | | X | Y |
| 1 | 70.50 | 2.60 | 29 | 50.70 | 36.50 |
| 2 | 70.50 | 0.00 | 30 | 50.70 | 33.50 |
| 3 | 64.25 | 0.00 | 31 | 54.00 | 36.50 |
| 4 | 61.65 | 0.00 | 32 | 56.60 | 36.50 |
| 5 | 40.35 | 0.00 | 33 | 67.90 | 36.50 |
| 6 | 37.75 | 0.00 | 34 | 70.50 | 36.50 |
| 7 | 31.50 | 0.00 | 36 | 70.50 | 22.35 |
| 8 | 28.90 | 0.00 | 37 | 70.50 | 19.75 |
| 9 | 8.85 | 0.00 | 38 | 50.95 | 19.15 |
| 10 | 6.25 | 0.00 | 39 | 56.85 | 17.05 |
| 11 | 0.00 | 0.00 | 41 | 53.85 | 16.55 |
| 12 | 0.00 | 2.60 | 42 | 61.00 | 6.70 |
| 13 | 0.00 | 6.75 | 43 | 58.40 | 5.35 |
| 14 | 0.00 | 9.75 | 44 | 32.65 | 27.80 |
| 15 | 0.00 | 12.75 | 45 | 33.35 | 25.20 |
| 17 | 0.00 | 33.50 | 47 | 26.35 | 18.65 |
| 18 | 0.00 | 36.50 | 48 | 25.35 | 15.65 |
| 19 | 3.30 | 36.50 | 50 | 39.00 | 16.55 |
| 20 | 5.90 | 36.50 | 51 | 44.90 | 19.15 |
| 21 | 19.80 | 36.50 | 52 | 42.00 | 16.55 |
| 22 | 19.80 | 33.90 | 53 | 34.70 | 10.55 |
| 23 | 25.35 | 36.50 | 54 | 34.70 | 7.95 |
| 24 | 25.35 | 33.90 | 55 | 12.60 | 27.65 |
| 25 | 39.25 | 36.50 | 56 | 11.60 | 25.05 |
| 26 | 41.85 | 36.50 | 58 | 10.85 | 10.30 |
| 27 | 45.15 | 36.50 | 59 | 10.85 | 7.70 |
| 28 | 45.15 | 33.50 | | | |

| | | |
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| DESCRIPTION: | PIM53 93X47 (SOLDER PIN) | PAGE 1 OF 1 |

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